

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE April 26, 2006	GROUP ART UNIT Unknown
(use several sheets if necessary)	APPLICANT(S): Nguyen et al.	

## REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
	B1	4,028,149	6/7/1977	Deines et al.		
	B2	4,254,590	3/10/1981	Eisele et al.		
	B3	5,242,863	9/7/1993	Xiang-Zheng et al.		
	B4	5,300,788	4/5/1994	Fan et al.		
	B5	5,374,564	12/20/1994	Bruel		
	B6	5,400,458	3/28/1995	Rambosek		
	B7	5,405,802	4/11/1995	Yamagata et al.		
	B8	5,559,043	9/24/1996	Bruel		
	B9	5,811,348	9/22/1998	Matushita et al.		
	B10	5,854,123	12/29/1998	Sato et al.		
	B11	5,877,070	3/2/1999	Goesele et al.		
	B12	5,909,627	6/1/1999	Egloff		
	B13	5,920,764	7/6/1999	Hanson et al.		
	B14	5,953,622	9/14/1999	Lee et al.		
	B15	5,966,620	10/12/1999	Sakaguchi et al.		
	B16	5,993,677	11/30/1999	Biasse et al.		
	B17	5,994,207	11/30/1999	Henley et al.		
	B18	6,013,563	1/11/2000	Henley et al.		
	B19	6,048,411	4/11/2000	Henley et al.		
	B20	6,054,370	4/25/2000	Doyle		
	B21	6,071,795	6/6/2000	Cheung et al.		
	B22	6,103,597	8/15/2000	Aspar et al.		
	B23	6,103,599	8/15/2000	Henley et al.		
	B24	6,127,199	10/3/2000	Inoue		
	B25	6,146,979	11/14/2000	Henley et al.		
	B26	6,150,239	11/21/2000	Goesele et al.		
	B27	6,190,998	2/20/2001	Bruel et al.		
	B28	6,225,190	5/1/2001	Bruel et al.		
	B29	6,271,101	8/7/2001	Fukunaga		
	B30	6,303,468	10/16/2001	Aspar et al.		
	B31	6,323,108	11/27/2001	Kub et al.		
	B32	6,323,109	11/27/2001	Okonogi		
	B33	6,346,458	2/12/2002	Bower		
	B34	6,513,564	2/4/2003	Bryan et al.		
	B35	6,534,380	3/18/2003	Yamauchi et al.		
	B36	6,607,969	8/19/2003	Kub et al.		
	B37	6,727,549	4/27/2004	Doyle		

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	B38 6,756,286	6/29/2004	Moriceau et al.		
	B39 6,770,507	8/3/2004	Abe et al.		
	B40 6,946,365	9/20/2005	Aspar et al.		
	B41 2002/0153563	10/24/2002	Ogura		
	B42 2002/0185684	12/12/2002	Campbell et al.		
	B43 2003/0162367	8/28/2003	Roche		
	B44 2003/0199105	10/23/2003	Kub et al.		

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES OR NO
	B45 EP 0 410 679 A1	1/30/1991	Europe		
	B46 EP 0 533 551 B1	3/9/2000	Europe		Abstract
	B47 EP 0 717 437 B1	4/24/2002	Europe		
	B48 EP 0 767 486 B1	1/2/2004	Europe		
	B49 EP 0 786 801A1	6/18/2003	Europe		Abstract
	B50 EP 0 793 263 A2	9/3/1997	Europe		
	B51 EP 0 801 419 A1	10/15/1997	Europe		Abstract
	B52 EP 0 807 970 A1	11/19/1997	Europe		Abstract
	B53 EP 0 902 843 B1	3/29/2000	Europe		Abstract
	B54 EP 0 917 193 A1	5/19/1999	Europe		
	B55 EP 0 925 888 B1	11/10/2004	Europe		
	B56 EP 0 938 129 A1	8/25/1999	Europe		
	B57 EP 1 014 452 B1	5/3/2006	Europe		
	B58 EP 1 050 901 A2	11/8/2000	Europe		
	B59 FR 2 681 472 A1	3/19/1993	France		Abstract
	B60 FR 2 748 850 A1	11/21/1997	France		Abstract
	B61 FR 2 748 851	11/21/1997	France		Abstract
	B62 FR 2 758 907 A1	7/31/1998	France		Abstract
	B63 FR 2 773 261	7/2/1999	France		Abstract
	B64 FR 2 774 510 A1	8/6/1999	France		Abstract
	B65 FR 2 781 925 A1	2/4/2000	France		Abstract
	B66 FR 2 796 491	1/19/01	France		Abstract
	B67 FR 2 797 347	2/9/2001	France		Abstract
	B68 FR 2 809 867	12/7/2001	France		Abstract
	B69 JP 62265717	11/18/1987	Japan		Abstract
	B70 JP 101004013	1/9/1989	Japan		Abstract
	B71 JP 07-254690	10/3/1995	Japan		Abstract

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	B72 JP 7-302889	11/14/1995	Japan		Abstract
	B73 JP 09-213594	8/15/1997	Japan		Abstract
	B74 JP 09-307719	11/28/1997	Japan		Abstract
	B75 JP 11045862	2/16/1999	Japan		Abstract
	B76 JP 11074208	3/16/1999	Japan		Abstract
	B77 JP 11-87668	3/30/1999	Japan		Abstract
	B78 JP 11-145436	5/28/1999	Japan		Abstract
	B79 JP 11-233449	8/27/1999	Japan		Abstract
	B80 WO 99/08316	2/18/1999	WIPO		Abstract
	B81 WO 99/35674 A1	7/15/1999	WIPO		Abstract
	B82 WO 99/39378	8/5/1999	WIPO		
	B83 WO 00/48238	8/17/2000	WIPO		Abstract
	B84 WO 01/11930A2	2/15/2001	WIPO		
	B85 WO 02/47156 A1	6/13/2002	WIPO		Abstract

EXAMINER INITIAL	OTHER ART - NON PATENT LITERATURE DOCUMENTS <small>(Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)</small>	
B86	Bruehl et al., [Vol. 99-1] Meeting Abstract No. 333, "Single-crystal semiconductor layer delamination and transfer through hydrogen implantation," <i>The 195th Meeting of The Electrochemical Society</i> , May 2-6, 1999, Seattle, Washington	
B87	Camperi-Ginestet et al., "Alignable Epitaxial Lift-off of GaAs Materials with Selective Deposition Using Polyimide Diaphragms", <i>IEEE Transactions Photonics Technology Letters</i> , Vol. 3, No. 12, December 1991, pp. 1123-1126	
B88	Demeester, et al., "Epitaxial Lift-off and its Applications", <i>Semicond. Sci. Technol.</i> , Vol. 8, 1993, pp. 1124-1135	
B89	DiCioccio et al., "III-V layer transfer onto silicon and applications", <i>Phys. Stat. Sol. (a)</i> , Vol. 202, No. 4., 2005, pp. 509-515/DOI 10.1002/pssa.200460411	
B90	Feijoo et al., "Prestressing of Bonded Wafers", Vol. 92-7 1992 pp. 230-238	
B91	Feng et al., "Generalized Formula for Curvature Radius and Layer Stresses Caused by Thermal Strain in Semiconductor Multilayer Structures", <i>J. Appl. Phys.</i> , Vol. 54, No. 1, 1983, pp. 83-85	
B92	Hamaguchi, et al., "Novel LSI/SOI Wafer Fabrication Using Device Layer Transfer Technique" <i>Proc. IEDM</i> , 1985, pp. 688-691	
B93	Kucheyev et al., "Ion implantation into GaN", <i>Materials Science and Engineering</i> , 33, 2001, pp. 51-107	
B94	Liu et al., "Ion implantation in GaN at liquid-nitrogen temperature: Structural characteristics and amorphization," <i>Physical Review B of The American Physical Society</i> , Vol. 57, No. 4, 1988, pp. 2530-2535	
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B95	Moriceau et al., [Vol. 99-1] Meeting Abstract No. 405, "A New Characterization Process Used to Qualify SOI Films," <i>The 195th Meeting of The Electrochemical Society</i> , May 2-6, 1999, Seattle, Washington.	
B96	Pollentier et al., "Fabrication of High-Radiance LEDs by Epitaxial Lift-off" <i>SPIE</i> , Vol. 1361, 1990, pp. 1056-1062	
B97	Suzuki et al., "High-Speed and Low Power n <sup>+</sup> -p <sup>+</sup> Double-Gate SOI CMOS", <i>IEICE Trans. Electron.</i> , Vol. E78-C, No. 4, April 1995, pp. 360-367	
B98	Timoshenko, S., "Analysis of Bi-Metal Thermostats", <i>J. Opt. Soc. Am.</i> , 11, 1925, pp. 233-256	
B99	Tong et al., "Low Temperature Si Layer Splitting", <i>Proceedings 1997 IEEE International SOI Conference</i> , Oct. 1997, pgs. 126-127	
B100	Wong et al., "Integration of GaN Thin Films with Dissimilar Substrate Materials by Pd-In Metal Bonding and Laser Lift-off", <i>Journal of Electronic Materials</i> , Vol. 28, No. 12, 1999, pp. 1409-1413	
B101	Yun et al., "Fractional Implantation Area Effects on Patterned Ion-Cut Silicon Layer Transfer," Dept. of Electrical Eng. And Computer Sciences, University of California, Berkeley, CA 94720, USA, 1999 IEEE International SOI Conference, Oct. 1999, pg. 129-30	
B102	Yun et al., "Thermal and Mechanical Separations of Silicon Layers from Hydrogen Pattern-Implanted Wafers," <i>Journal of Electronic Materials</i> , Vol. No. 36, No. 8 2001	

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